

## **Amendments to the Claims**

### **LISTING OF CLAIMS**

Claims 1-77 (canceled).

78. (new) A method for fabricating a semiconductor component comprising:

providing a substrate;  
forming a plurality of openings in the substrate; and  
at least partially filling the openings with solder.

79. (new) The method of claim 78 wherein the filling step is performed using a capillary action.

80. (new) The method of claim 78 wherein the filling step is performed using a solder wave.

81. (new) The method of claim 78 wherein the solder comprises a solder metal.

82. (new) The method of claim 78 wherein the substrate comprises a semiconductor material.

83. (new) The method of claim 78 wherein the substrate comprises a semiconductor die.

84. (new) The method of claim 78 wherein the substrate comprises a semiconductor wafer.

85. (new) The method of claim 78 wherein the forming the plurality of openings step comprises laser machining.

86. (new) The method of claim 78 wherein the forming the plurality of openings step comprises etching.

87. (new) The method of claim 78 wherein the forming the plurality of openings step comprises dry etching.

88. (new) The method of claim 78 wherein the forming the plurality of openings step comprises laser machining and etching.

89. (new) The method of claim 78 wherein the forming the plurality of openings step comprises laser machining and dry etching.

90. (new) A method for fabricating a semiconductor component comprising:

providing a substrate having a first side and a second side;

forming a plurality of openings in the substrate extending from the first side to the second side; and

forming a plurality of conductive members in the openings by depositing solder into the openings.

91. (new) The method of claim 90 wherein the forming the conductive members step is performed using a solder wave.

92. (new) The method of claim 90 wherein the forming the conductive members step is performed using capillary action.

93. (new) The method of claim 90 wherein the solder comprises a solder metal.

94. (new) The method of claim 90 further comprising forming a plurality of first contacts on the first side in electrical contact with the conductive members.

95. (new) The method of claim 90 further comprising forming a plurality of second contacts on the second side in electrical contact with the conductive members.

96. (new) The method of claim 90 further comprising prior to the forming the conductive members step forming a plurality of insulating layers in the openings.

97. (new) The method of claim 90 wherein the substrate comprises a semiconductor wafer.

98. (new) The method of claim 90 wherein the substrate comprises a plurality of semiconductor dice contained on a semiconductor wafer.

99. (new) A method for fabricating a semiconductor component comprising:

providing a substrate having a first side and a second side;

forming a plurality of openings in the substrate extending from the first side to the second side; and

forming conductive members in the openings by exposing the openings to solder.

100. (new) The method of claim 99 wherein the forming the conductive members step is performed using a solder wave and the solder comprises a solder metal.

101. (new) The method of claim 99 wherein the forming the conductive members step is performed using capillary action.

102. (new) The method of claim 99 wherein the conductive members comprise solder plugs which completely fill the openings.

103. (new) The method of claim 99 wherein the conductive members comprise layers of solder on sidewalls of the openings.

104. (new) The method of claim 99 wherein the forming the plurality of openings step comprises laser machining.

105. (new) The method of claim 99 wherein the substrate comprises a semiconductor material and further comprising forming insulating layers in the openings prior to the forming the conductive members step.

106. (new) The method of claim 99 further comprising forming a plurality of first contacts on the first side in electrical communication with the conductive members.

107. (new) The method of claim 99 further comprising forming a plurality of second contacts on the second side in electrical communication with the conductive members.

108. (new) The method of claim 99 wherein the substrate comprises a semiconductor material.